## UT54ACS08/UT54ACTS08

## Features

- $0.6 \mu$ CRH CMOS
- Latchup immune
- High speed
- Low power consumption
- Single 5 volt supply
- Available QML Q or V processes
- 14-lead flatpack
- UT54ACS08 - SMD 5962-96518
- UT54ACTS08 - SMD 5962-96519


## Description

The UT54ACS08 and UT54ACTS08 are quadruple two-input AND gates. The circuits perform the Boolean functions $Y=A \cdot B$ or $Y=\overline{\bar{A}+\bar{B}}$ in positive logic.

The devices are characterized over full military temperature range of $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$.

## Function Table

| Input |  | Output |
| :---: | :---: | :---: |
| A | B | Y |
| H | H | H |
| L | X | L |
| X | L | L |

## Logic Symbol



## Note:

1) Logic symbol in accordance with ANSI/IEEE standard 91-1984 and IEC Publication 617-12.

Quadruple 2-Input AND Gates

## UT54ACS08/UT54ACTS08

## Pinouts



## Logic Diagram



## UT54ACS08/UT54ACTS08

Operational Environment ${ }^{1}$

| Parameter | Limit | Units |
| :--- | :---: | :---: |
| Total Dose | 500 K | $\mathrm{rads}(\mathrm{Si})$ |
| SEU Threshold ${ }^{2}$ | 80 | $\mathrm{MeV}-\mathrm{cm}^{2} / \mathrm{mg}$ |
| SEL Threshold | 120 | $\mathrm{MeV}^{2} \mathrm{~cm}^{2} / \mathrm{mg}$ |
| Neutron Fluence | 1.0 E 14 | $\mathrm{n} / \mathrm{cm}^{2}$ |

## Notes:

1) Logic will not latchup during radiation exposure within the limits defined in the table.
2) Device storage elements are immune to SEU affects.

## Absolute Maximum Ratings

| Symbol | Parameter | Limit | Units |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}$ | Supply voltage | -0.3 to 7.0 | V |
| $\mathrm{~V}_{\mathrm{I} / 0}$ | Voltage any pin | -.3 to $\mathrm{V}_{\mathrm{DD}}+.3$ | V |
| $\mathrm{~T}_{\text {STG }}$ | Storage Temperature range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Maximum junction temperature | +175 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{LS}}$ | Lead temperature (soldering 5 seconds) | +300 | ${ }^{\circ} \mathrm{C}$ |
| $\Theta_{\text {JC }}$ | Thermal resistance junction to case | $15.5(\mathrm{ACS})$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{I}_{\mathrm{I}}$ | DC input current | $15.0(\mathrm{ACTS})$ | $\pm 10$ |
| $\mathrm{P}_{\mathrm{D}}$ | Maximum power dissipation | 1 | mA |

## Note:

1) Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## Recommended Operating Conditions

| Symbol | Parameter | Limit | Units |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}$ | Supply voltage | 4.5 to 5.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Input voltage any pin | 0 to $\mathrm{V}_{\mathrm{DD}}$ | V |
| $\mathrm{T}_{\mathrm{C}}$ | Temperature range | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |

## UT54ACS08/UT54ACTS08

## DC Electrical Characteristics ${ }^{7}$

( $\mathrm{V}_{\mathrm{DD}}=5.0 \mathrm{~V} \pm 10 \%$; $\mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V}^{6},-55^{\circ} \mathrm{C}<\mathrm{T}_{\mathrm{C}}<+125^{\circ} \mathrm{C}$ ); Unless otherwise noted, Tc is per the temperature range ordered.

| Symbol | Parameter |  | Condition | MIN | MAX | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| VIL | Low-level input voltage ${ }^{1}$ <br> ACTS <br> ACS |  |  |  | $\begin{gathered} 0.8 \\ .3 V_{D D} \end{gathered}$ | V |
| $\mathrm{V}_{\mathrm{IH}}$ | High-level input voltage ${ }^{1}$ ACTS ACS |  |  | $\begin{aligned} & .5 \mathrm{~V}_{\mathrm{DD}} \\ & .7 \mathrm{~V}_{\mathrm{DD}} \end{aligned}$ |  | V |
| $\mathrm{I}_{\text {IN }}$ | Input leakage current ACTS/ACS |  | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}$ or $\mathrm{V}_{\text {SS }}$ | -1 | 1 | $\mu \mathrm{A}$ |
| VoL | Low-level output voltage ${ }^{3}$ ACTS <br> ACS |  | $\begin{aligned} & \mathrm{I}_{\mathrm{OL}}=8.0 \mathrm{~mA} \\ & \mathrm{IoL}^{2}=100 \mu \mathrm{~A} \end{aligned}$ |  | $\begin{aligned} & 0.40 \\ & 0.25 \end{aligned}$ | V |
| VOH | High-level output voltage ${ }^{3}$ ACTS ACS |  | $\begin{aligned} & \mathrm{I}_{\mathrm{OH}}=-8.0 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-100 \mu \mathrm{~A} \end{aligned}$ | $\begin{gathered} .7 V_{D D} \\ V_{D D}-0.25 \end{gathered}$ |  | V |
| Ios | Short-circuit output current ${ }^{2,4}$ ACTS/ACS |  | $\mathrm{V}_{\mathrm{O}}=\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{S S}$ | -200 | 200 | mA |
| IoL | Output current ${ }^{10}$ (sink) |  | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{VoL}_{\mathrm{oL}}=0.4 \mathrm{~V} \end{aligned}$ | 8 |  | mA |
| $\mathrm{I}_{\text {OH }}$ | Output current ${ }^{10}$ (source) |  | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{~V}_{\mathrm{OH}}=\mathrm{V}_{\mathrm{DD}}-0.4 \mathrm{~V} \end{aligned}$ | -8 |  | mA |
| $P_{\text {total }}$ | Power dissipation 2,8,9 |  | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ |  | 1.8 | $\begin{aligned} & \hline \mathrm{mW} / \\ & \mathrm{MHz} \end{aligned}$ |
| $\mathrm{I}_{\text {DDQ }}$ | Quiescent Supply Current | Pre-Rad | $\begin{aligned} & V_{I N}=V_{D D} \text { or } V_{S S} \\ & V_{D D}=V_{D D} M A X \end{aligned}$ |  | 10 |  |
|  |  | Post-Rad Device Type 01 |  |  | 50 | $\mu \mathrm{A}$ |
| $\Delta \mathrm{I}_{\text {DDQ }}$ | Quiescent Supply Current Delta ACTS |  | For input under test $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}-2.1 \mathrm{~V}$ <br> For all other inputs $V_{I N}=V_{D D} \text { or } V_{S S}$ $V_{D D}=5.5 \mathrm{~V}$ |  | 1.6 | mA |
| $\mathrm{CIN}_{\text {IN }}$ | Input capacitance ${ }^{5}$ |  | $f=1 \mathrm{MHz} @ 0 \mathrm{~V}$ |  | 15 | pF |
| Cout | Output capacitance ${ }^{5}$ |  | $f=1 \mathrm{MHz} @ 0 \mathrm{O}$ |  | 15 | pF |

## UT54ACS08/UT54ACTS08

## Notes:

1) Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $\mathrm{V}_{\mathrm{IH}}=\mathrm{V}_{\mathrm{IH}}(\mathrm{min})+$ $20 \%,-0 \% ; \mathrm{V}_{\mathrm{IL}}=\mathrm{V}_{\text {IL }}(\max )+0 \%,-50 \%$, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $\mathrm{V}_{\mathrm{IH}}(\mathrm{min})$ and $\mathrm{V}_{\text {IL }}(\mathrm{max})$.
2) Supplied as a design limit but not guaranteed or tested.
3) Per MIL-PRF-38535, for current density $\leq 5.0 \mathrm{E} 5 \mathrm{amps} / \mathrm{cm}^{2}$, the maximum product of load capacitance (per output buffer) times frequency should not exceed $3,765 \mathrm{pF} / \mathrm{MHz}$.
4) Not more than one output may be shorted at a time for maximum duration of one second.
5) Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and $\mathrm{V}_{\mathrm{ss}}$ at frequency of 1 MHz and a signal amplitude of 50 mV rms maximum.
6) Maximum allowable relative shift equals 50 mV .
7) Device type 01 is only offered with a TID tolerance guarantee of 1 E 5 rads( Si ), 3 E 5 rads $(\mathrm{Si})$, and $5 \mathrm{E} 5 \mathrm{rads}(\mathrm{Si})$, and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.
8) Power does not include power contribution of any TTL output sink current.
9) Power dissipation specified per switching output.
10) This value is guaranteed based on characterization data, but not tested.

## AC Electrical Characteristics ${ }^{2}$

$\left(\mathrm{V}_{\mathrm{DD}}=5.0 \mathrm{~V} \pm 10 \%\right.$; $\mathrm{V}_{S S}=0 \mathrm{~V}^{1},-55^{\circ} \mathrm{C}<\mathrm{TC}<+125^{\circ} \mathrm{C}$ ); Unless otherwise noted, Tc is per the temperature range ordered.

| Symbol | Parameter | Minimum | Maximum | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{t}_{\text {PHL }}$ | Input to Yn | 1 | 13 | ns |
| $\mathrm{t}_{\text {PLH }}$ | Input to Yn | 1 | 10 | ns |

## Notes:

1) Maximum allowable relative shift equals 50 mV .
2) Device type 01 is only offered with a TID tolerance guarantee of 1 E 5 rads( Si ), 3 E 5 rads( Si ), and 5 E 5 rads( Si$)$, and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.

Quadruple 2-Input AND Gates

## UT54ACS08/UT54ACTS08

## Packages



## UT54ACS08/UT54ACTS08

## UT54ACS08/UT54ACTS08: SMD



## Notes:

1) Lead finish ( $A, C$, or $X$ ) must be specified.
2) If an " $X$ " is specified when ordering, part marking will match the lead finish and will be either " $A$ " (solder) or " $C$ " (gold).
3) Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening. For prototype inquiries, contact factory.
4) Device type 01 is only offered with a TID tolerance guarantee of $1 \mathrm{E} 5 \mathrm{rads}(\mathrm{Si}), 3 \mathrm{E} 5 \mathrm{rads}(\mathrm{Si})$, and $5 \mathrm{E} 5 \mathrm{rads}(\mathrm{Si})$, and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.

## Datasheet Revision History

| Revision Date | Description of Change | Author |
| :---: | :--- | :---: |
| $10-17$ | Page 4 edited IDDQ <br> Applied new CAES Data Sheet template to the document. | RT |
| $1-18$ | Updates to reflect current SMD | RT |

## UT54ACS08/UT54ACTS08

Datasheet Definitions

| Advanced Datasheet | CAES reserves the right to make changes to any products and services <br> deccribed herein at any time without notice. The product is still in the <br> development stage and the datasheet is subject to change. <br> Specifications can be TBD and the part package and pinout are not final. |
| :--- | :--- |
| Preliminary Datasheet | CAES reserves the right to make changes to any products and services <br> described herein at any time without notice. The product is in the <br> characterization stage and prototypes are available. |
| Datasheet | Product is in production and any changes to the product and services <br> described herein will follow a formal customer notification process for <br> form, fit or function changes. |

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